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Hagen and Griessen Reply: Although Chaddah and Bhagwat¹ point out rightly in their Comment that the relaxation rate of the magnetization M of a superconductor depends on the field profile inside the sample at time $t=0$, we show here that their argument is based on a wrong expression for $M=M(t)$.

In several publications²⁻⁴ we have shown, on the basis of Monte Carlo simulations as well as of an exact solution of a four-pinning-region model, that over approximately 90% of the relaxation

$$M(t) = M(t=0) \left[1 - \frac{kT}{E(T)} \ln \left(1 + \frac{t}{\tau} \right) \right], \quad (1)$$

if (i) the sample is homogeneous, in the sense that all pinning centers are described by the same activation energy $E(T)$, and (ii) the field has initially completely penetrated the sample so as to establish a critical state. These two conditions guarantee that everywhere the current density j is equal to the critical current j_c at $t=0$. For $t \gg \tau$ (as is the case in all experiments carried out so far) Eq. (1) reduces to Eq. (1) in the Comment.

In Eq. (3), Chaddah and Bhagwat¹ assume without derivation that the same logarithmic time dependence is valid for the case where the field has not penetrated the sample completely at $t=0$, i.e., when $H < H^*$. We show here that this assumption which has also been made by many other authors (see, e.g., Refs. 5-9) is, in fact, not justified.

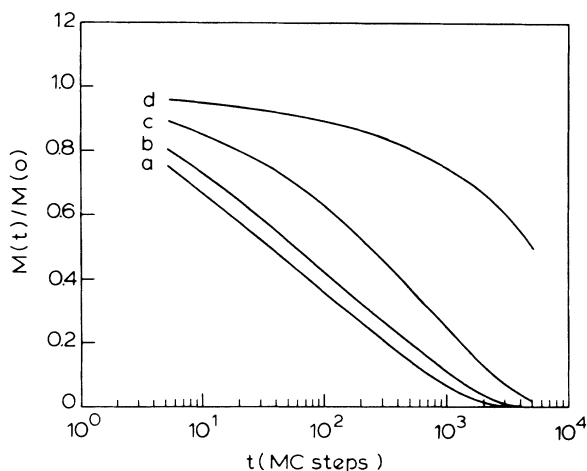


FIG. 1. Magnetization relaxation normalized to its value at $t=0$ for a sample containing twenty pinning centers as obtained from Monte Carlo simulations. For the fully field-penetrated sample a , the density of flux lines at $t=0$ decreases from 1300 at the surfaces of the slab to 400 at the center of the sample. For sample b , the density of flux lines decreases from 900 at the surfaces to zero at the center. This corresponds to $H=H^*$. For the partially penetrated samples c and d , the density is 500 and 100, respectively, at the surface. The density gradient (i.e., the critical current) and $E/kT=7.5$ is the same for all samples. The time is indicated in units of Monte Carlo (MC) steps.

For this we consider a slab of thickness $2a$ and infinite dimensions in the y and z directions in a magnetic field H applied along the z axis. At $t=0$, $|j|=j_c$ in a surface sheet $x_0 < |x| < a$, and $j=0$ in the central part, $|x| \leq x_0$, of the sample. Using the same Monte Carlo simulation as in Refs. 3 and 10 we obtain the relaxation curves shown in Fig. 1 for various cases of fully and partially field-penetrated samples. For the partially penetrated samples, $M(t)$ does not obviously vary linearly with $\ln t$ and the relaxation rate $dM/d \ln t$ is not uniquely defined; i.e., $A(H)$ in Eq. (3) of Chaddah and Bhagwat is, in fact, strongly *time dependent*. An analytic expression for $A(H, T, t)$ will be published elsewhere.¹⁰ It is important to point out that convex M vs $\ln t$ curves in partially penetrated $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_x$ single crystals have been observed by Shi, Xu, and Umezawa⁸ (e.g., at 8 K in a field of 0.1 T).

In conclusion, we do not believe that a maximum in $d \ln M / d \ln t$ can satisfactorily be explained with the arguments put forward by the authors. It is, however, obvious that relaxation processes in partially field-penetrated samples have to be taken into account for a correct description of flux creep at low fields and temperatures.

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